

Nikolay Arutyunov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Formation and annealing of vacancy-P complexes in proton-irradiated germanium. <i>Acta Materialia</i> , 2015, 100, 1-10.	7.9	11
2	Monovacancy-As complexes in proton-irradiated Ge studied by positron lifetime spectroscopy. <i>Acta Materialia</i> , 2015, 83, 473-478.	7.9	10
3	Positron probing of point V-group impurity-vacancy complexes in \hat{I}^3 -irradiated germanium. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 788-793.	4.0	7
4	Positron Annihilation Rate and Broad Component of 1D-ACAR in Cz-Si and Fz-Si. <i>Solid State Phenomena</i> , 1997, 57-58, 489-494.	0.3	4
5	Positron Trapping by Oxygen-Related Defects in Silicon and Anisotropy of 1D-ACAR Spectra. <i>Solid State Phenomena</i> , 1999, 69-70, 333-338.	0.3	4
6	Positron annihilation in AlN and GaN. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 110-113.	2.7	3
7	Investigation of vacancy-type complexes in GaN and AlN using positron annihilation. <i>Semiconductors</i> , 2002, 36, 1106-1110.	0.5	3
8	Configuration of DV Complexes In Ge: Positron Probing of Ion Cores. <i>Solid State Phenomena</i> , 2008, 131-133, 89-94.	0.3	3
9	Cascade phonon-assisted trapping of positrons by divacancies in n-FZ-Si(P) single crystals irradiated with 15 MeV protons. <i>AIP Conference Proceedings</i> , 2014, , .	0.4	3
10	Positron probing of disordered regions in neutron-irradiated silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 2175-2179.	1.5	3
11	Positron annihilation lifetime in float-zone n-type silicon irradiated by fast electrons: a thermally stable vacancy defect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 807-811.	0.8	3
12	Positron Studies of Thermal-Induced Defects in Silicon. <i>Solid State Phenomena</i> , 1989, 6-7, 435-442.	0.3	2
13	Positron Annihilation on Thermal Defects in Cz-Si and Fz-Si. <i>Solid State Phenomena</i> , 1993, 32-33, 589-594.	0.3	2
14	Elementally specific electron-positron annihilation radiation emitted from ion cores of group-V impurity-vacancy complexes in germanium. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 609-612.	2.7	2
15	Similarity of Atomic Configurations of Thermally Stable Positron-Sensitive Complexes Produced with 0.9-MeV Electrons and 15-MeV Protons in \hat{I}^3 -irradiated FZ-Si Crystals. <i>Solid State Phenomena</i> , 0, 242, 296-301.	0.3	2
16	Positron probing of open vacancy volume of phosphorus-vacancy complexes in float-zone n-type silicon irradiated by 0.9-MeV electrons and by 15-MeV protons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700120.	0.8	1
17	Positron-sensitive vacancy-type centres in the nitrides: 1D-ACAR data. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 412-415.	2.7	0
18	Point Defects in \hat{I}^3 -Irradiated Germanium: High- and Low- Momentum Positron Annihilation Study Before and After n-p-Conversion. <i>Solid State Phenomena</i> , 2009, 156-158, 455-460.	0.3	0

#	ARTICLE	IF	CITATIONS
19	Microstructure of bismuth centers in silicon before and after irradiation with 15 MeV protons. Journal of Physics Condensed Matter, 2021, 33, 245702.	1.8	0